# VS-U5FX60FA120

### Vishay Semiconductors



FRED Pt<sup>®</sup> Gen 5 Hyperfast Rectifier Diode, 1200 V, 60 A



PRIMARY CHARACTERISTICS							
V <sub>R</sub>	1200 V						
V <sub>F</sub> (typical) at 30 A, per diode	2.91 V						
t <sub>rr</sub> (typical) at 30 A, per diode	41 ns						
$I_{F(DC)}$ per module at $T_C = 85 \ ^{\circ}C$	60 A						
Туре	Modules - diode, FRED Pt <sup>®</sup>						
Package	SOT-227						
Circuit configuration	Two separate diodes, parallel pin-out						

### **FEATURES**

losses trade off

Hyperfast and optimized Q<sub>rr</sub>



- RoHS COMPLIANT
- · Optimized for high speed operation
- 175 °C maximum operating junction temperature
- · Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- Designed and gualified for industrial level
- UL approved file E78996
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, the VS-U5FX60FA120 is the right choice for high frequency converters, both soft switched / resonant. The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters, and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Cathode to anode voltage	V <sub>R</sub>		1200	V			
Continuous forward current per diode	I <sub>F</sub>	T <sub>C</sub> = 85 °C	30	^			
Single pulse forward current per diode	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	150	A			
Maximum power dissipation per module	PD	T <sub>C</sub> = 85 °C	164	W			
RMS isolation voltage	VISOL	Any terminal to case, t = 1 min	2500	V			
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	1200	-	-		
For all allows	V <sub>FM</sub>	I <sub>F</sub> = 30 A	-	2.91	3.57	V	
Forward voltage		VFM	I <sub>F</sub> = 30 A, T <sub>J</sub> = 150 °C	-	2.19	-	
		V <sub>R</sub> = 1200 V	-	0.5	60		
Reverse leakage current	I <sub>RM</sub>	$T_{\rm J} = 125 \ ^{\circ}{\rm C}, \ V_{\rm R} = 1200 \ {\rm V}$	-	60	-	μA	
		T <sub>J</sub> = 150 °C, V <sub>R</sub> = 1200 V	-	214	-		

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DYNAMIC RECOVERY CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time	+	$T_J = 25 \ ^\circ C$		-	41	-	ns	
Reverse recovery lime	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	68	-		
Poole recovery ourrent	1	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 30 A, di <sub>F</sub> /dt = 1000 A/μs, V <sub>R</sub> = 800 V	-	19	-	A	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	32	-		
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		-	0.8	-	μC	
neverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	2.3	-	μΟ	
Junction capacitance	CT	V <sub>R</sub> = 1200 V, f	= 1 MHz	-	13.4	-	pF	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance junction to case, per diode	<b>D</b>		-	-	1.1	
Thermal resistance junction to case, per module	R <sub>thJC</sub>		-	-	0.55	°C/W
Thermal resistance case to heatsink, per module	R <sub>thCS</sub>	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
		Torque per diode	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style				SO	Г-227	•





Fig. 1 - Typical Forward Voltage Drop Characteristics



Fig. 2 - Typical Values of Reverse Current





I<sub>F</sub> - Continuous Forward Current (A) Fig. 3 - Maximum Allowable Case Temperature vs.

Average Forward Current (Per Diode)



Fig. 4 - Average Power Loss vs. Average Forward Current



Fig. 5 - Junction Capacitance vs. Reverse Voltage



Fig. 6 - Diode Reverse Recovery Time vs. dl<sub>F</sub>dt



Fig. 7 - Diode Reverse Recovery Current vs. dI<sub>F</sub>dt



Fig. 8 - Diode Reverse Recovery Charge vs. dl<sub>F</sub>dt

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Fig. 9 - Maximum Thermal Impedance Junction to Case

### **ORDERING INFORMATION TABLE**

Device code	vs-	U5F	х	60	F	Α	120	
	1	2	3	4	5	6	(7)	
		<ul> <li>Vishay Semiconductors product</li> <li>U5F = Gen 5 FRED Pt<sup>®</sup> family</li> <li>X = Hyperfast FRED Pt<sup>®</sup> diode</li> </ul>						
	4 - 5 -		Current rating per module ( $60 = 60 \text{ A}$ ) F = circuit configuration (two separate diodes, parallel pin-out)					
	6 - 7 -		0	dicator ( ng (120			dard ins	ulated base)

CIRCUIT CONFI	GURATION	
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two separate diodes, parallel pin-out	F	Lead Assignment 4 1 1 1 1 1 1 1 1 1 1 1 1 1

LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95423			
Packaging information		www.vishay.com/doc?95425			
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**Vishay Semiconductors** 



SOT-227 Generation 2

### **DIMENSIONS** in millimeters (inches)



#### Note

• Controlling dimension: millimeter



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